

HIGH VOLTAGE POWER SCHOTTKY RECTIFIER

MAIN PRODUCT CHARACTERISTICS

PRELIMINARY DATASHEET

$I_{F(AV)}$	2 x 10A
V_{RRM}	60V
V_F (typ)	0.58V

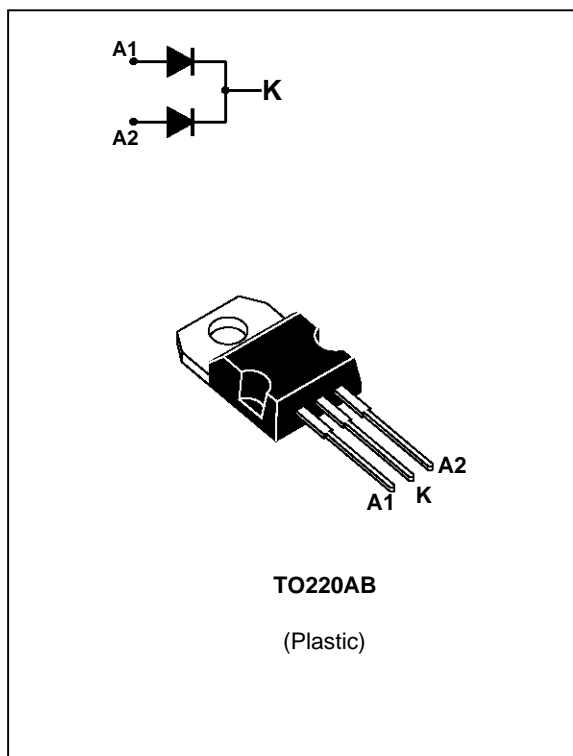
FEATURES AND BENEFITS

- NEGLIGIBLE SWITCHING LOSSES
- LOW FORWARD VOLTAGE DROP
- LOW CAPACITANCE
- HIGH REVERSE AVALANCHE SURGE CAPABILITY

DESCRIPTION

High voltage dual Schottky rectifier suited for switchmode power supplies and other power converters.

Packaged in TO220AB, this device is intended for use in medium voltage operation, and particularly, in high frequency circuitries where low switching losses and low noise are required.



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter		Value	Unit
V_{RRM}	Repetitive peak reverse voltage		60	V
$I_{F(RMS)}$	RMS forward current	Per diode	30	A
$I_{F(AV)}$	Average forward current	$T_c=110^{\circ}C$ $V_R = 60V$ $\delta = 0.5$ Per diode Per device	10 20	A A
I_{FSM}	Surge non repetitive forward current	$t_p=10ms$ sinusoidal Per diode	200	A
I_{RRM}	Repetitive peak reverse current	$t_p=2\mu s$ $F=1KHz$ Per diode	1	A
I_{RSM}	Non repetitive peak reverse current	$t_p=100\mu s$ Per diode	1	A
T_{stg}	Storage temperature range		- 65 to + 150	$^{\circ}C$
T_j	Max. Junction temperature		150	$^{\circ}C$
dV/dt	Critical rate of rise of reverse voltage		1000	$V/\mu s$

STPS2060CT

THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
Rth (j-c)	Junction to case	Per diode	1.6	°C/W
		Total	0.9	
Rth (c)	Coupling		0.15	°C/W

When the diodes 1 and 2 are used simultaneously :

$$T_j - T_c(\text{diode } 1) = P(\text{diode } 1) \times R_{th(j-c)}(\text{Per diode}) + P(\text{diode } 2) \times R_{th(c)}$$

ELECTRICAL CHARACTERISTICS (Per diode)

STATIC CHARACTERISTICS

Symbol	Parameter	Test Conditions		Min.	Typ.	Max.	Unit
I _R *	Reverse leakage current	V _R = V _{RRM}	T _j = 25°C			70	μA
			T _j = 125°C			33	mA
V _F **	Forward voltage drop	I _F = 20 A	T _j = 125°C			0.8	V
		I _F = 10 A	T _j = 125°C		0.58	0.67	
		I _F = 20 A	T _j = 25°C			0.94	
C	Capacitance	60 V, 1MHz	T _j = 125°C		150		pF

Pulse test : * t_p = 5 ms, duty cycle < 2 %

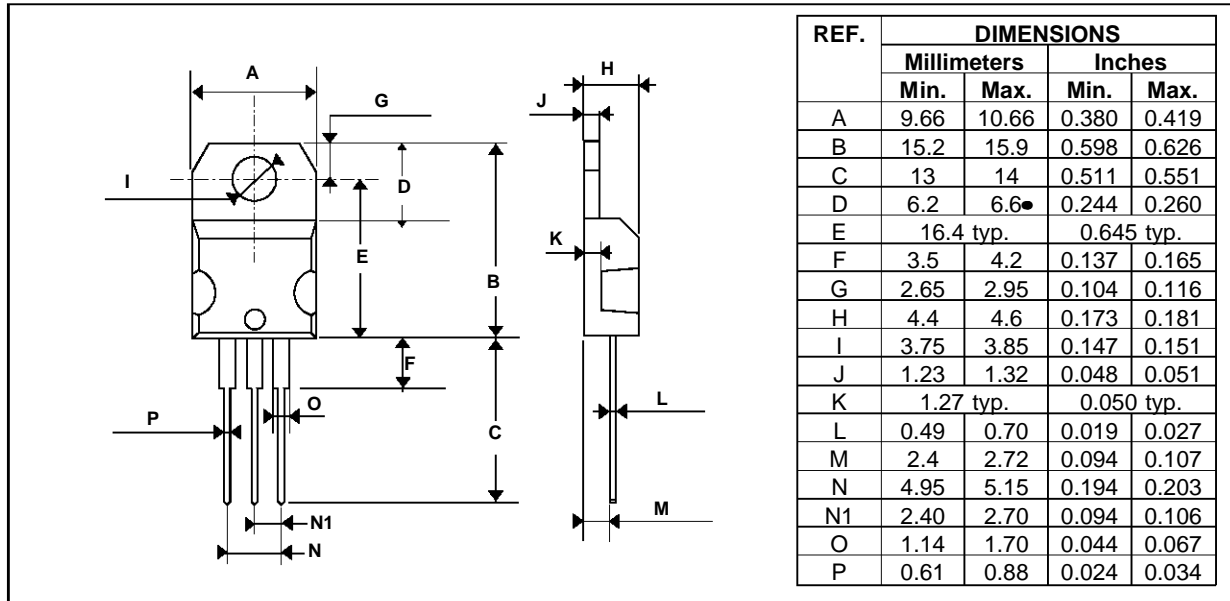
** t_p = 380 μs, duty cycle < 2 %

To evaluate the conduction losses use the following equation :

$$P = 0.54 \times I_F(AV) + 0.013 \times I_F^2(RMS)$$

PACKAGE MECHANICAL DATA (millimeters)

TO220AB Plastic



Cooling method : by conduction (methode C)

Marking : Type number

Weigth : 2 g

Recommended torque value : 0.8m.N

Maximum torque value : 1m.N

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